56. (original) A low selectivity deposition method comprising:

placing a substrate in a first chamber;

forming a first part of a nucleation layer on a first surface of the substrate in the first chamber;

forming a second part of a nucleation layer on a second surface of the substrate in the first chamber;

removing the substrate from the first chamber and placing it in a second chamber different from the first; and

forming a layer of a first chemisorbed specie at least one monolayer thick on the first and second parts of the nucleation layer in the second chamber substantially non-selectively on the first part of the nucleation layer compared to the second part.

57. (original) The deposition method of claim 56 wherein the forming the first and the second part of the nucleation layer occurs simultaneously and the nucleation layer forms substantially non-selectively on the first surface of the substrate compared to the second surface.

58. (original) The deposition method of claim 56 wherein the first surface of the substrate exhibits a property of chemisorbing the first specie at a slower rate compared to the second surface.

59. (original) The deposition method of claim 56 wherein the first surface comprises borophosphosilicate glass and the second surface comprises polysilicon.

60. (previously presented) The deposition method of claim 9 wherein the first and second parts of the nucleation layer comprise aluminum oxide.

61. (previously presented) The deposition method of claim 9 wherein the first and second parts of the nucleation layer comprise tantalum oxide.

62. (previously presented) The deposition method of claim 10 wherein CVD of the nucleation layer occurs non-selectively at a temperature no greater than about 645 ° C and at a pressure of from about 500 milliTorr to about 1.5 Torr.

63. (previously presented) The deposition method of claim 11 wherein ALD of the nucleation layer occurs non-selectively at a temperature of from about 400 to about 550 ° C and at a pressure of from about 100 milliTorr to about 20 Torr.

64. (previously presented) The deposition method of claim 9 wherein the forming the deposition layer is performed ex situ of the forming the first and the second part of the nucleation layer.

65. (previously presented) The deposition method of claim 27 wherein forming the first and second parts of the nucleation layer occurs simultaneously and comprises depositing a complete nucleation layer in a single deposition, the complete nucleation layer and the combined first and second specie layers consisting essentially of same components in approximately same proportions.

66. (previously presented) The deposition method of claim 31 wherein simultaneously forming the first and second parts of the nucleation layer comprises non-selective CVD at a temperature no greater than about 645 ° C and at a pressure of from about 500 milliTorr to about 1.5 Torr.

67. (previously presented) The deposition method of claim 31 wherein simultaneously forming the first and second parts of the nucleation layer comprises non-selective ALD at a temperature of from about 400 to about 550 ° C and at a pressure of from about 100 milliTorr to about 20 Torr.

68. (previously presented) The deposition method of claim 38 wherein simultaneously forming the first and second parts of the nucleation layer comprises depositing a complete nucleation layer in a single deposition, the complete nucleation layer and the combined initiation and deposition layers consisting essentially of same components in approximately same proportions.

69. (previously presented) The deposition method of claim 47 wherein ALD of the nucleation substance occurs at a temperature of from about 400 to about 550 ° C and at a pressure of from about 100 milliTorr to about 20 Torr.